

Enhanced gallium nitride FET Family adds 100-V, 16 milli-Ohm power transistor



Efficient Power Conversion

Corporation introduced its EPC2016 enhancement mode gallium nitride power transistors. This a 3.36-mm², 100-V_{DS}, 11-A device includes a maximum R_{DS(on)} of 16 mΩ with 5 V applied to the gate. This GaN power transistor presents high performance due to its ultra high switching frequency, extremely low R_{DS(on)}, exceptionally low QG and in a very small package. Applications include high-speed DC-DC power supplies, point-of-load converters, class D audio amplifiers, and high frequency circuits. Additionally, the company's EPC9010 development board, featuring the EPC2016 devices and the LM5113 gate driver IC in a half bridge configuration supports designers in evaluating and incorporating eGaN FETs into their power conversion systems.

Efficient Power Conversion Corporation, www.epc-co.com [1]

Source URL (retrieved on 01/28/2015 - 3:47pm):

<http://www.ecnmag.com/product-releases/2013/09/enhanced-gallium-nitride-fet-family-adds-100-v-16-milli-ohm-power-transistor>

Links:

[1] <http://www.epc-co.com>